

■ Features

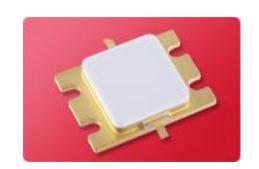
High Power: 570W(Typ.) @ Pin=39.8W(46dBm)
High Efficiency: 58%(Typ.) @ Pin=39.8W(46dBm)

· Broad Band: 3.1 to 3.5GHz

Impedance Matched Zin/Zout = 50 ohmHermetically Sealed Package: IV-Package

Description

Sumitomo Electric's GaN-HEMT SGN3135-500H-R offers high power, high efficiency and greater consistency covering 3.1 to 3.5 GHz for S-band radar applications with 50V operation and pulse condition of up to 200µsec pulse width and duty of up to 10%.



ABSOLUTE MAXIMUM RATING (Case Temperature T_c=25 deg.C)

Item	Symbol	Rating	Unit
Operating Voltage	V_{DS}	55	V
Drain-Source Voltage	V_{DS}	250 @ V _{GS} =-10V	V
Gate-Source Voltage	V_{GS}	-15	V
Storage Temperature	T _{stg}	-55 to +125	deg.C
Channel Temperature	T _{ch}	+250	deg.C

RECOMMENDED OPERATING CONDITION

RECOMMENDED OF EXAMING CONDITION					
Item	Symbol	Condition	Limit	Unit	
Drain-Source Voltage	V_{DS}		<=50	V	
Forward Gate Current	I_{GF}	Rg=5.1ohm	<=508	mA	
Reverse Gate Current	I_{GR}	Rg=5.1ohm	>=-21.3	mA	
Peak Channel Temperature	T _{ch-peak}		<=200	deg.C	
Pulse Width	PW	Duty 10%	<= 200	μsec	

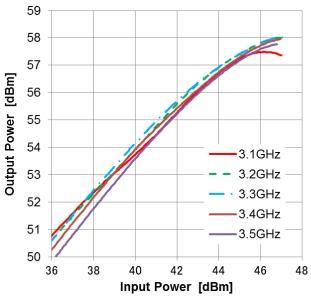
ELECTRICAL CHARACTERISTICS (Case Temperature T_c=25 deg.C)

Item	Symbol	Condition	Limit			Unit
Item			Min.	Тур.	Max.	Unit
Pinch-off Voltage	V_P	V_{DS} =50V, I_{DS} =150mA	-4.0	-3.0	-2.0	V
Output Power	P_{out}		480	570	=	W
Drain Efficiency	DE	$V_{DS} = 50V$, $I_{DS(DC)} = 1500$ mA,	-	58	-	%
Power Gain	G_P	Pin=39.8W(46 dBm),	10.8	11.6	-	dB
Gain Flatness	GF	f=3.1, 3.2, 3.3, 3.4, 3.5GHz, PW=200µsec, Duty=10%	-	0.6	1.3	%
Load Mismatch Ruggedness	VSWR	, ,	10:1	-	-	dB
Thermal Resistance	R_{th}	Channel to Case at 105W P _{DC}	-	0.55	0.7	deg.C/W

CASE STYLE	IV
RoHS Compliance	YES

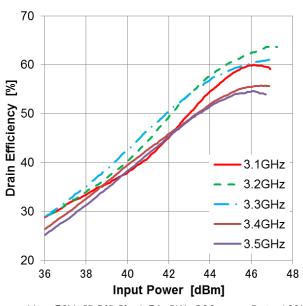


■ Typical Performance



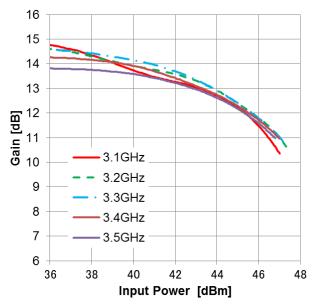
V_{DS}=50V, IDS(DC)=1.5A, PW=200msec, Duty 10%

Figure 1. Output Power vs Input Power



 V_{DS} =50V, IDS(DC)=1.5A, PW=200msec, Duty 10%

Figure 3. Drain Efficiency vs Input Power



 V_{DS} =50V, IDS(DC)=1.5A, PW=200msec, Duty 10%

Figure 2. Gain vs Input Power

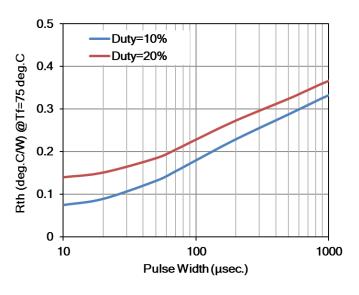
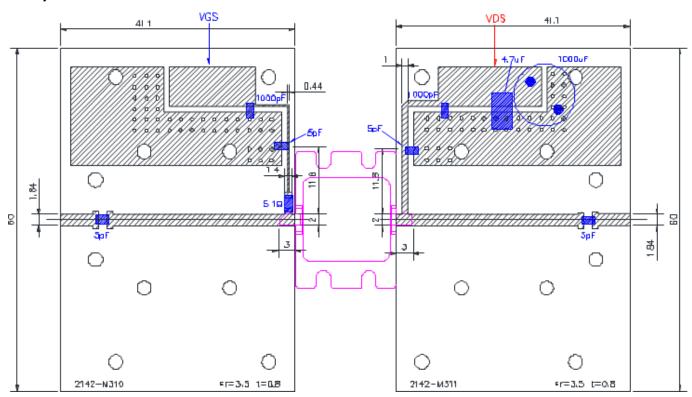


Figure 4. Transient Thermal Resistance



■ Test Fixture

TF/SGN3135-500H-R



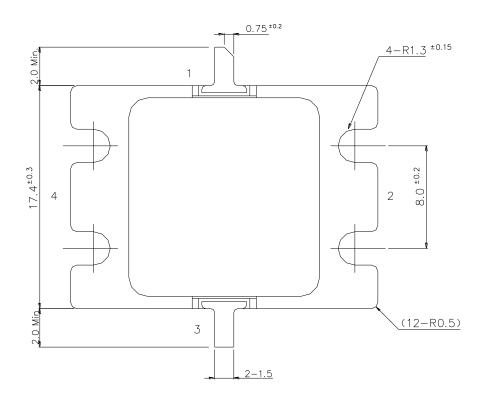
PCB: h=0.8mm, er=3.5, Cu=18um

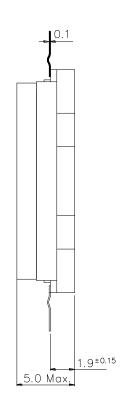
Unit: mm

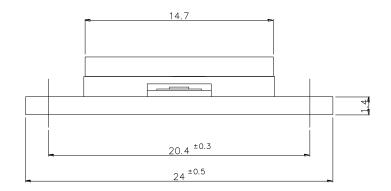


■ Package Outline

Case Style: IV







1:Gate

2:Source(Flange)

3:Drain

4 : Source(Flange)

Unit : mm



For Safety, Observe the Following Procedures Environmental Management

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Respect all applicable laws of the country when discarding this product.
 This product must be disposed in accordance with methods specified by applicable hazardous waste procedures.

Any information, such as descriptions of a function and examples of application circuits, in this document are presented solely as a reference for the purpose to show examples of operations and uses of Sumitomo Electric semiconductor device(s); Sumitomo Electric does not warrant the proper operation of the device(s) with respect to its use based on such information. When the user develops equipment incorporating the device(s) based on such information, they must assume full responsibility arising out of using such information. Sumitomo Electric assumes no liability for any damages whatsoever arising out of the use of the information.

Any information in this document, including descriptions of function and schematic diagrams, shall not be construed as a license for the use or exercise of any intellectual property right, such as patent right or copyright, or any other right of Sumitomo Electric or any third party nor does Sumitomo Electric warrant non-infringement of any third-party's intellectual property right or other right by using such information. Sumitomo Electric assumes no liability for any infringement of the intellectual property rights or other rights of third parties which would result from the use of information contained herein.

The products described in this document are designed, developed and manufactured as contemplated for general use, including, without limitation, ordinary industrial use, general office use, personal use, and household use, but are not designed, developed and manufactured as contemplated (1) for use accompanying fatal risks or dangers that, unless extremely high safety is secured, could have a serious effect to the public, and could lead directly to death, personal injury, severe physical damage or other loss (i.e., nuclear reaction control in nuclear facility, aircraft flight control, air traffic control, mass transport control, medical life support system, missile launch control in weapon system), or (2) for use requiring extremely high reliability (i.e., submersible repeater and artificial satellite). Please note that Sumitomo Electric will not be liable to the user and/or any third party for any claims or damages arising from the aforementioned uses of the products.

Any semiconductor devices have an inherent chance of failure. You must protect against injury, damage or loss from such failures by incorporating safety design measures into your facility and equipment such as redundancy, fire protection, and prevention of excessive current levels and other abnormal operating conditions.

If any products described in this document represent goods or technologies subject to certain restrictions on export under the Foreign Exchange and Foreign Trade Law of Japan, the prior authorization of the Japanese government will be required for export of those products from Japan.

http://www.sedi.co.jp/

ATTENTION

Information in this document is subject to change without notice.